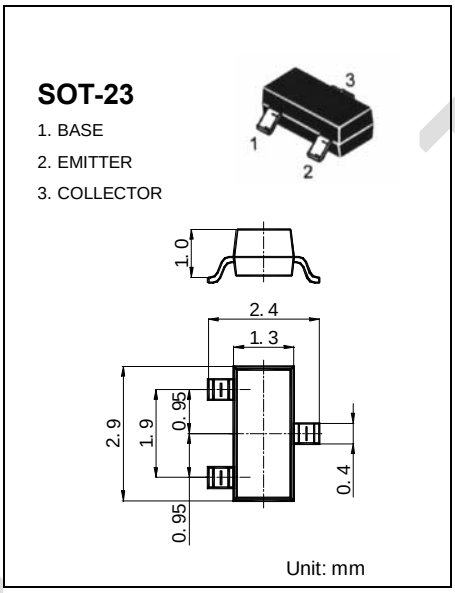
SOT-23 Plastic-Encapsulate Transistors

BCW61B TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.25 W (Tamb=25℃)

Collector current

$I_{CM:}$ -0.2 A

Collector-base voltage

$V_{(BR)CBO:}$ -32 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -10μA, I_E=0	-32			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -1mA, I_B=0	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-32V, I_E=0			-0.02	μA
Collector cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-0.02	μA
DC current gain	h_{FE}	V_{CE}=-5V, I_C= -2mA	180		310	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-50mA, I_B=-1.25mA			-0.55	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=-50mA, I_B=-1.25mA			-1.05	V
Transition frequency	f_T	V_{CE}= -5V, I_C=-10mA f=100MHz	100			MHz

Marking	**BB**